OPB732, OPB732WZ



Features:

- PC board mounting (OPB732)
- 24" (610 mm) 26 AWG wired with mounting tabs (OPB732WZ)
- Non-contact infrared switch
- Up to 1" or more reflective distance depending on circuitry



Description:

OPB732 uses an Infrared LED and Phototransistor in a reflective switch configuration. The assembly is offered with either PCBoard through hole pins (**OPB732**) or 24" (610 mm), 26 AWG wires (**OPB732WZ**), and uses an opaque housing to reduce the sensor's ambient light sensitivity. The emitter and sensor are protected by a clear window, providing a device that can operate in a dusty environment. The phototransistor can be configured as a Common Collector or Common Emitter device.

While an object is in the reflective path of the device, light from the LED will be reflected back to the housing irradiating the surface (base) of the phototransistor. When Infrared light strikes the phototransistor, the transistor becomes forward biased and is considered to be in the "ON" state, providing an $I_{C(ON)}$ current proportional to the light striking the phototransistor. With the Infrared light from the LED not being reflected to the phototransistor, the phototransistor turns "OFF," minimizing the $I_{C(ON)}$ current.

Custom electrical, wire and cabling and connectors are available. Contact your local representative or OPTEK for more information.

Applications:

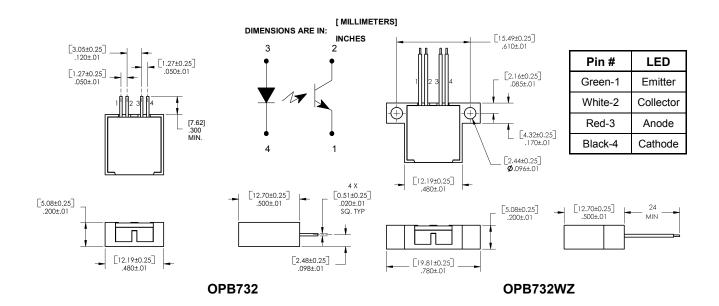
- Non-contact reflective object sensor
- · Assembly line automation
- Machine automation
- Equipment security
- Door sensor
- Machine safety
- End of travel sensor

Ordering Information							
Part Number	LED Peak Wavelength	Lead Length / Spacing					
OPB732	850 nm	0.150"/ see diagram					
OPB732WZ	030 11111	24" / 26 AWG Wire					



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Electrical Specifications

Absolute	Maximum Ratings (T _A = 25° C unless o	otherw	ise not	ed)				
Storage Temperature						-40° C to +100° C		
Operating Temperature							-40° C to +85° C	
Lead Soldering Temperature (1/16" (1.6mm) from case for 5 seconds with soldering iron) (2)						260° C		
LED								
Forward Current							50 mA	
Peak Forward current (2 μs pulse width, 0.1% Duty Cycle)						1 A		
Reverse DC Voltage							3 V	
Power Dissipation						100 mW		
Output Photo Transistor								
Collector-Emitter Voltage 3							30 V	
Collector DC Current							50 mA	
Power Dissipation						100 mW		
Electrical Characteristics (T _A = 25° C unless otherwise noted)								
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS		
Input LED (See OP265 for additional information, reference only)								
V_{F}	Forward Voltage	-	-	1.8	V	I _F = 20 mA		
I _R	Reverse Current	-	-	100	μΑ	V _R = 2 V		
Output Phototransistor (See OP505 for additional information, reference only)								

 $V_{(BR)CEO}$

 I_{CEO}

Coupled						
V _{CE(SAT)}	Collector-Emitter Saturation Voltage ⁽⁴⁾	-	-	0.4	V	$I_C = 250 \mu\text{A}, I_F = 30 \text{mA}$, (4)
I _{C(ON)}	On-State Collector Current ⁽⁴⁾	0.25	-	-	mA	$V_{CE} = 1 V, I_F = 30 mA, (4)$
I _{CX}	Cross Talk	-	-	50	μΑ	$V_{CE} = 5 \text{ V, } I_F = 30 \text{ mA,}$ No reflective surface

100

nΑ

Notes:

- (1) All parameters tested using pulse technique.
- (2) RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering.
- (3) Methanol or isopropanol are recommended as cleaning agents. The plastic housing is soluble in chlorinated hydrocarbons and keytones.
- (4) Distance = 1" (from front of package to a 90% diffuse reflective white card)

Collector-Emitter Breakdown Voltage

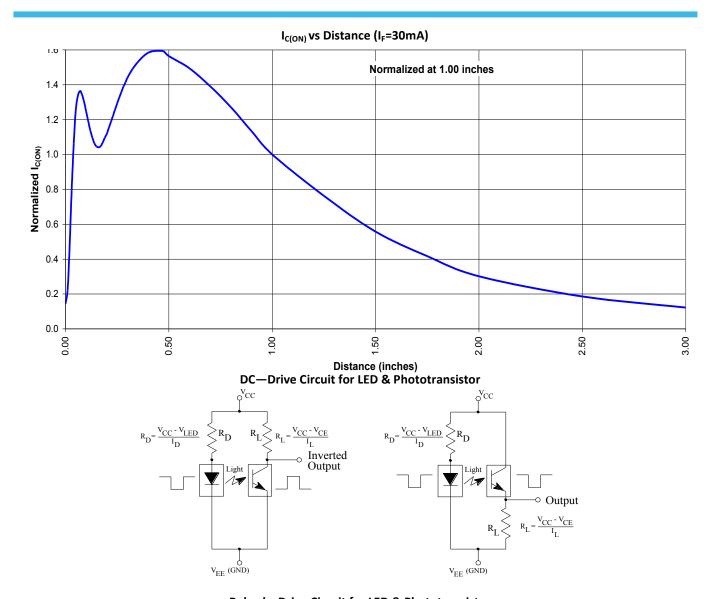
Collector-Emitter Dark Current

 $I_C = 100 \, \mu A, E_E = 0 \, \text{mw/cm}^2$

 $V_{CE} = 10 \text{ V}, E_{E} = 0 \text{ mw/cm}^{2}$

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Pulsed—Drive Circuit for LED & Phototransistor

